

Monitoring Single Scattering Events in Single Quantum Dots

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The quantum-jump approach is used for a theoretical description of resonance luminescence from a *single* semiconductor quantum dot in contact with its solid-state environment. For continuous excitation of the single-exciton groundstate the luminescence exhibits bright periods, where photons are spontaneously emitted from the exciton decay, which are interrupted by dark periods when one electron or hole suffers a spin flip. It is shown that continuously monitored resonance luminescence provides a very sensitive measure of such rare single scattering events in quantum dots.

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Semiconductor quantum dots (QDs) consist of a small island of lower-bandgap material embedded in a solid-state matrix of higher-bandgap material [1]. Proper choice of the material and dot parameters thus can give rise to confinement of a few carrier states within this lower-bandgap region. Because of the resulting discrete atomic-like density-of-states, semiconductor QDs have been referred to as *artificial atoms*. When optical experiments are performed on large QD ensembles, all the available samples still suffer from the effects of inhomogeneity and dispersion in dot size. A major advancement in the field has come from different types of local optical experiments, that allow the investigation of individual QDs: Extremely narrow linewidths have been reported from single-dot spectroscopy [2], and first time-resolved measurements indicate carrier lifetimes a few orders of magnitude larger than typically observed in semiconductors of higher dimension [3].

Theoretically the system *dot interacting with environment* is conveniently described within a density-matrix description [4]. Adopting the approximation of Fermi's golden rule, at each instant of time the dot system is then completely determined by its density matrix ρ (with the diagonal and off-diagonal elements providing information about state occupation and coherence, respectively), and environment interactions are accounted for by instantaneous scattering events. Because of its statistical nature, the elements of ρ have to be interpreted either as the ensemble average over a large number of identical dots, or, for ergodic systems, as the average over a sufficiently long measurement time. Apparently, when performing time-resolved measurements on single dots the situation is substantially different. Thus, the most interesting questions arise: Does the interpretation of optical experiments of *single* dots require theoretical concepts beyond the usual density-matrix description for the carrier dynamics in semiconductor nanostructures [4], and can time-resolved single-dot measurements provide additional information as opposed to ensemble-dot measurements?

As we will show in the following, the answer to both questions is: Yes. It is worth noting that related ques-

tions first arose almost a decade ago, when it became possible to store single ions in a Paul trap and to continuously monitor their resonance fluorescence (see Ref. [5] for a review). In the seminal work of Dalibard *et al.* [6], the authors showed for a V-scheme, where the ground-state 0 of an atom is coupled to a short-lived state 1 and to a metastable state 2, that the fluorescence of the laser-driven system exhibits long dark periods, associated to the excitation of the extremely weak $0 \leftrightarrow 2$ transition, which are followed by bright periods with many photon emissions from the decay of the short-lived state 1.

In this paper, we propose to use continuous laser excitation and continuous monitoring of luminescence for the observation of *single* spin-flip processes in semiconductor QDs. Contrary to the proposal of Dalibard *et al.*, within our scheme the rare scattering events originate from the coupling of the QD carriers to the elementary excitations of their solid-state environment. Thus, the dot serves as a *sensor* of its environment, which makes possible the observation of the otherwise almost inaccessible rare scattering events. Besides the most challenging prospect of measuring single scatterings in solid state [7], the long-lived spin excitations in QDs have recently attracted strong interest [8–10] because of their potential utilization for quantum-information processing [11,12].

Figure 1 sketches the proposed scheme: A single QD is located inside an ideal broadband counter with unit efficiency and coverage of all angles [13] (grey circle). Initially, all valence-band states of the dot are occupied and all conduction-band states are empty. When the pump laser ω_p is turned on, an electron is promoted from the valence to the conduction band, where the photogenerated electron and hole (i.e., the missing valence-band electron) have opposite spin orientations. Because of the coherence of the driving laser the system starts to undergo Rabi-type oscillations, i.e., the electron is transferred back and forth between the valence and conduction band. These oscillations are interrupted by spontaneous emissions of photons γ from the decay of electron-hole (exciton) states $X_{o,b}^\pm$, where, after detection of γ , the system is reset back to the vacuum state, and the Rabi-type oscillations start

again. After some time, however, due to environment coupling the spin of either the electron or hole is flipped (see $\otimes$ in Fig. 1); since each QD state can be occupied at most by two carriers with *opposite* spin orientations, after such a spin flip the system becomes optically inactive (i.e., no further electron-hole pair can be excited by the pump laser). This can be also inferred from Fig. 2(a) which shows results of a simulation of resonance luminescence from a single QD (for details see further below): After turning on the pump pulse at time $t = 0$, photons are emitted by spontaneous decay of $X_{o,b}^\pm$ and are detected as single photon counts. These bright periods are then interrupted by dark periods with zero photon count, which indicate the occurrence of a spin flip process. It finally requires a second spin flip to bring back the system to the bright sector, and to turn on luminescence again.

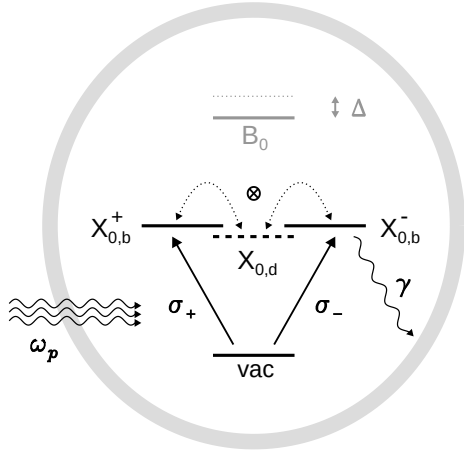


FIG. 1. Schematic illustration of the proposed experimental setup, where a single QD is surrounded by a 4π photon detector (with unit efficiency) which detects all spontaneously emitted photons γ . The linearly polarized pump pulse (ω_p) couples the vacuum state to the optically allowed groundstate excitons $X_{o,b}^\pm$; B_o denotes the biexciton groundstate, whose energy is by an amount of Δ smaller than $2E_{X_{o,b}^\pm}$ due to correlation effects. Spin-flip processes (indicated by $\otimes$) couple the optically allowed states $X_{o,b}^\pm$ with the optically forbidden $X_{o,d}$ ones, which, because of the electron-hole exchange interaction, have a slightly smaller energy.

The theoretical framework accounting for the coherent laser excitation and the detection of single photon emissions is conveniently provided by the *quantum-jump approach* [5]. Here, the central idea is that the broadband photon counting can be approximately described by a series of repeated *gedanken* measurements at times $t_n = n \cdot \Delta_t$ ($n = 0, 1, 2, \dots$) [14], where as observable the projector on the photon vacuum $\mathbb{P}_0 = |0_\gamma\rangle\langle 0_\gamma|$ indicates whether a photon has been emitted or not. If at time t_o the system is described by the density matrix ρ_o , the density matrix at time t_n *provided that no photons have been emitted in the interval* $[t_o, t_n]$ is given by [5,14]:

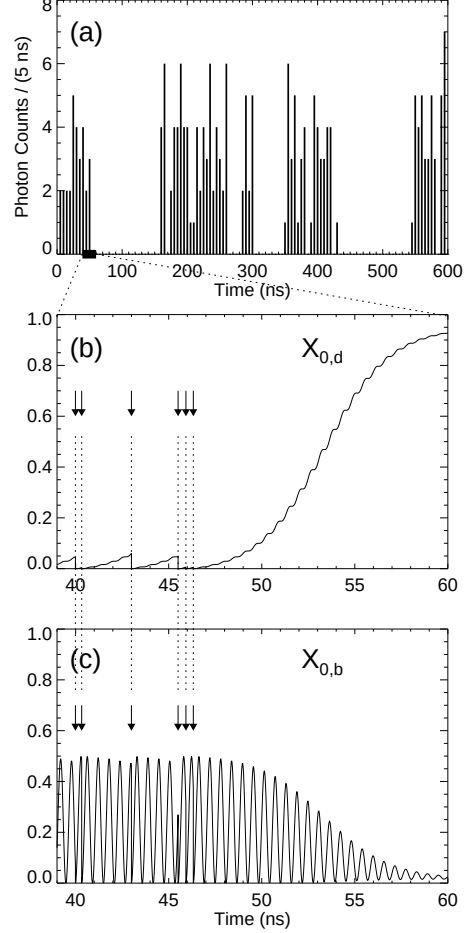


FIG. 2. Results of our Monte-Carlo simulations for resonance luminescence from a single QD: (a) histogram of photon emission (with bin width of 5 ns); (b,c) trajectory of $\rho_{xx}^{(0)}/\text{tr}(\rho)$ for $x = X_{o,d}, X_{o,b}^\pm$. The arrows indicate times of photon detection. Prototypical dot and laser parameters of $\Delta = 2$ meV and $\Omega_p^\pm = 10$ μ eV are used. For the energy splitting δ between $X_{o,b}^\pm$ and $X_{o,d}$ we assume $\delta \ll T$, thus obtaining the same scattering rates for $X_{o,b}^\pm \rightarrow X_{o,d}$ and $X_{o,d} \rightarrow X_{o,b}^\pm$; we use $(2\Gamma^s)^{-1} = 50$ ns and $(2\Gamma^\gamma)^{-1} = 0.86$ ns for the radiative decay, which corresponds to the bulk-GaAs value.

$$\rho_{t_n}^{(0)} = \mathbb{P}_0 U(t_n, t_{n-1}) \dots \mathbb{P}_0 U(t_1, t_o) \rho_o \times U^\dagger(t_1, t_o) \mathbb{P}_0 \dots U^\dagger(t_n, t_{n-1}) \mathbb{P}_0, \quad (1)$$

where $U(t_n, t_{n-1})$ is the time evolution operator from t_{n-1} to t_n , and the superscript on $\rho^{(0)}$ indicates the requirement of no-photon emission. The quantity $P_0(t) = \text{tr}(\rho_t^{(0)})$ then gives the probability that, starting at time t_o with ρ_o , no photons are emitted up to time t ; apparently, $P_0(t)$ is a monotonically decreasing function since the probability of photon emission will increase with time. If finally at time t_n a photon is detected, we know that the system has changed to the one-photon subspace $\rho^{(1)}$ (we assume that Δ_t is short enough and only *one* photon is emitted per interval). What the photon detector does,

however, is to absorb the photon and to reset the density matrix to [14]:

$$|0_\gamma\rangle \text{tr}_\gamma(\mathbb{P}_1 U(t_n, t_{n-1}) \rho_{t_{n-1}}^{(0)} U^\dagger(t_n, t_{n-1}) \mathbb{P}_1) \langle 0_\gamma| / \text{tr}(), \quad (2)$$

with $\mathbb{P}_1 = \mathbf{1} - \mathbb{P}_0$, and the denominator ensures that $\text{tr}(\rho) = 1$ after detection of γ .

In this work we apply the above scheme to the resonance luminescence of exciton states in a single QD. Quite generally, the driving laser can not only excite single excitons but also multi-exciton states (e.g., biexcitons). Thus, we use x to denote generic multi-exciton states, with $N_x = 0, 1, 2, \dots$ the number of electron-hole pairs; the corresponding dot Hamiltonian is of the form $\sum_x E_x |x\rangle\langle x|$, with E_x the multi-exciton energies. The coupling to the pump laser with electric field $\mathcal{E}_p^\sigma(t) = \mathcal{E}_p^\sigma \cos(\omega_p t)$ is described within the usual rotating-wave and dipole approximations, $-\frac{1}{2} \sum_{\sigma, xx'} \Omega_p^\sigma (e^{i\omega_p t} \mathcal{P}_{xx'}^\sigma + e^{-i\omega_p t} \mathcal{P}_{xx'}^{\sigma*}) |x'\rangle\langle x|$, where: $\sigma = \pm 1$ denotes left- and right-hand circular polarization, respectively (we assume that, as in most semiconductors, electron-hole pairs with given spin orientation can be selectively created by circular polarized light); $\Omega_p^\sigma = \mu_o \mathcal{E}_p^\sigma$ is the Rabi frequency with μ_o the dipole element of the bulk semiconductor; $\mathcal{P}_{xx'}^\sigma = \int d\mathbf{r} \langle x' | \hat{\psi}_{h,-\sigma}(\mathbf{r}) \hat{\psi}_{e,\sigma}(\mathbf{r}) | x \rangle$, with $\hat{\psi}_{e,\sigma}^\dagger$ ($\hat{\psi}_{h,\sigma}^\dagger$) creating an electron (hole) with spin orientation σ . The spontaneous radiative decay of dot states is accounted for by the Hamiltonian $\sum_{\mathbf{k}\sigma, xx'} i g_k^\gamma (a_{\mathbf{k}\sigma}^\dagger \mathcal{P}_{xx'}^\sigma - a_{\mathbf{k}\sigma} \mathcal{P}_{xx'}^{\sigma*}) |x'\rangle\langle x|$, where $g_k^\gamma = \mu_o (2\pi\omega_k)^{\frac{1}{2}}$, $a_{\mathbf{k}\sigma}^\dagger$ creates a photon with wavevector $\mathbf{k}$ and circular polarization σ , and $\omega_k = ck/n$ is the photon energy (with c the speed of light and n the semiconductor refraction index).

Spin-flip scatterings in III-V semiconductors are conveniently described as a two-step process [10,16]: First, spin-orbit coupling introduces a small mixing of electron (hole) states with different spin orientations; second, environment coupling (e.g., to phonons) mediates transitions between states with different spin orientations. While in semiconductors of higher dimensionality all different types of elastic and quasi-elastic scatterings contribute to such spin-flip processes [16,17], in semiconductor QDs severe phase-space restrictions lead to a strong suppression, and first experimental results indicate extremely long spin coherence times [8,9]. As a genuine model accounting for spin flips in QDs we consider, within the spirit of Ref. [11], a Caldeira-Leggett-type model where a set of harmonic oscillators (assumed to be in thermal equilibrium) is coupled linearly to the system spins by $\sum_j g_j^s \mathbf{S} \cdot (\mathbf{b}_j + \mathbf{b}_j^\dagger) / \sqrt{2}$; here $\mathbf{b}_j$ are bosonic operators whose free motion is governed by $\sum_j \omega_j^s \mathbf{b}_j^\dagger \cdot \mathbf{b}_j$, and g_j^s is the coupling constant to the carriers in the dot.

Next, we assume that the time interval Δ_t of successive *gedanken* experiments is short as compared to the time evolution of multi-exciton states due to the driving pump

laser, but long as compared to ω_p^{-1} ; thus, in the evaluation of U of Eq. (1) we perform the Markov and adiabatic approximations. Using the interaction representation according to $\sum_x \Delta_x |x\rangle\langle x|$ (with $\Delta_x = E_x - N_x \cdot \omega_p$), we then find within second order perturbation theory for the time evolution of the conditional density matrix $\rho^{(0)}$ [14,18]:

$$\dot{\rho}^{(0)} = -i(h_o \rho^{(0)} - \rho^{(0)} h_o^\dagger) + \hat{\mathcal{J}}^s \rho^{(0)}, \quad (3)$$

with $\dot{\rho}_{t_n}^{(0)} \equiv (\rho_{t_n}^{(0)} - \rho_{t_{n-1}}^{(0)}) / \Delta t$, the effective Hamiltonian $(h_o)_{xx'} = \delta_{xx'} \Delta_x - \frac{1}{2} \sum_\sigma \Omega_p^\sigma (\mathcal{P}_{xx'}^\sigma + \mathcal{P}_{xx'}^{\sigma*}) - i(\Gamma_{xx'}^\gamma + \Gamma_{xx'}^s)$, where $\Gamma^{\gamma,s}$ are out-scattering contributions due to photon and spin interactions, and $\hat{\mathcal{J}}^s$ accounts for spin-flip induced in-scatterings [19] (note that because of our restriction to the zero-photon subspace there are no corresponding in-scatterings due to photon decay). Finally, whenever a photon is detected the density matrix is reset to $\rho^{(0)} \rightarrow \hat{\mathcal{J}}^\gamma \rho^{(0)} / \text{tr}()$, with the reset matrix $\hat{\mathcal{J}}^\gamma$ [19].

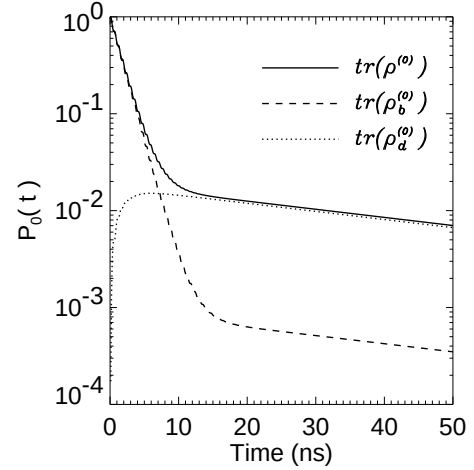


FIG. 3. Time-dependent probability $P_0(t)$ of no-photon emission for a coherently driven system which is in the groundstate at time 0 (same parameters as in Fig. 2). The solid line corresponds to $\text{tr}(\rho^{(0)})$, whereas the dotted and dashed lines show the contributions of $\langle X_{o,d} | \rho^{(0)} | X_{o,d} \rangle$ and remainder.

In our calculations we use prototypical dot parameters, which correspond to the model structure presented in Ref. [15] (see figure caption 2), and for the pump laser we assume linear polarization (i.e., $\mathcal{E}_p^+ = \mathcal{E}_p^-$) and photon energy ω_p tuned to the groundstate-exciton energy (see Fig. 1). Because excited single-exciton states are energetically separated from $E_{X_{o,b}^\pm}$ by the order of the confinement energy (~ 10 – 50 meV for most dots [1]), for moderate Rabi frequencies they do not couple to the driving laser and are therefore neglected in our analysis. As the only multi-exciton state we consider the biexciton groundstate B_o , which approximately consists of $X_{o,b}^+ + X_{o,b}^-$ (with other multi-exciton states again energetically well separated). In Ref. [8] spin dephasing times $\tau_s \sim 3$ ns have

been reported, which, however, have been dominated by inhomogeneous broadening. Thus, as a representative value within a single dot we here assume a value of 50 ns. Smaller values of τ_s would not change the qualitative behavior of our results, as long as they would be significantly longer than the radiative lifetime ~ 1 ns. Fig. 3 shows the probability $P_0(t)$ that up to time t no photon has been emitted. At times below ~ 10 ns the time evolution is governed by the optical decay of the laser-excited exciton states $X_{o,b}^\pm$; with increasing time, however, the probability of a spin-flip process increases and becomes dominant at later times. Because spin-forbidden transitions do not couple to the light, in this regime $P_0(t)$ decreases only very slowly and the decay is determined by additional spin-flip processes bringing back the system to the bright sector. We used these results to perform Monte-Carlo simulations of resonance luminescence from a single QD (Fig. 2) [5]: At time t_o , we start with a density matrix ρ_o ; the time of the next-photon emission is then determined by use of a random number $r \in [0, 1)$ from $r = 1 - P_0(t)$ (in the numerical solution of Eq. (3) we neglect the time discretization Δ_t); finally, after a photon count the density matrix is set back to $\hat{J}^\gamma \rho^{(0)} / \text{tr}()$, and the simulation starts again. Fig. 2(c) shows a single history of the occupation of $X_{o,b}^\pm$: Rabi-type oscillations are interrupted by sudden jumps (arrows), associated to the detection of emitted photons; correspondingly, the dark-exciton contributions (Fig. 2(b)) slowly increase in time, and are reset back to zero after photon detection (note the beginning of a dark period at later times in Figs. 2(b,c)). Finally, Fig. 2(a) shows the histogram of emitted photons: One clearly observes bright and dark sectors, whose lengths are determined by τ_s . Experimental observation of single spin flips requires coherent excitation of single QDs and efficient continuous broadband counting of photons on a timescale of nanoseconds.

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$$\Gamma_{x'x}^\gamma = \sum_{\sigma, \bar{x}} \alpha^\gamma(\omega_{x\bar{x}}) \mathcal{P}_{x\bar{x}}^\sigma \mathcal{P}_{x\bar{x}}^{\sigma*} \quad (4a)$$

$$\Gamma_{x'x}^s = \sum_{\sigma, \bar{x}} \alpha_T^s(\omega_{x\bar{x}}) \mathcal{S}_{x\bar{x}}^\sigma \mathcal{S}_{x\bar{x}}^{\sigma*} \quad (4b)$$

$$\mathcal{J}_{xx', \bar{x}\bar{x}'}^\gamma = \sum_{\sigma} (\alpha^\gamma(\omega_{\bar{x}x}) + \alpha^\gamma(\omega_{x'\bar{x}'})) \mathcal{P}_{x\bar{x}}^\sigma \mathcal{P}_{x'\bar{x}'}^{\sigma*} \quad (4c)$$

$$\mathcal{J}_{xx', \bar{x}\bar{x}'}^s = \sum_{\sigma} (\alpha_T^s(\omega_{\bar{x}x}) + \alpha_T^s(\omega_{x'\bar{x}'})) \mathcal{S}_{x\bar{x}}^\sigma \mathcal{S}_{x'\bar{x}'}^{\sigma*}, \quad (4d)$$

with the spectral distribution function $\alpha^\lambda(\omega) = \pi \sum_{\ell} (g_{\ell}^\lambda)^2 \delta(\omega - \omega_{\ell}^\lambda)$ ($\lambda = \gamma, s$ and $\ell = \mathbf{k}, j$), and the thermally broadened function $\alpha_T^\lambda(\omega) = \theta(\omega)(n(\omega) + 1)\alpha^\lambda(\omega) + \theta(-\omega)n(-\omega)\alpha^\lambda(-\omega)$, where $n(\omega)$ is the Bose-Einstein distribution at temperature T . Finally, $\mathcal{S}_{x'x} = \langle x' | S^{-\sigma} | x \rangle$ is the overlap between states x and x' when one electron or hole flips spin.

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